

## P-Channel Enhancement Mode Power MOSFET

### DESCRIPTION

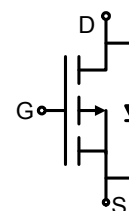
The HM3407B uses advanced trench technology to provide excellent  $R_{DS(ON)}$ . This device is suitable for use as a load switch or in PWM applications.

### GENERAL FEATURES

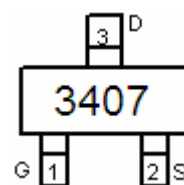
- $V_{DS} = -30V, I_D = -4.1A$   
 $R_{DS(ON)} < 95m\Omega @ V_{GS} = -4.5V$   
 $R_{DS(ON)} < 65m\Omega @ V_{GS} = -10V$
- High Power and current handling capability
- Lead free product is acquired
- Surface Mount Package

### Application

- PWM applications
- Load switch
- Power management



Schematic diagram



Marking and pin Assignment



SOT-23 top view

### Package Marking And Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
3407	HM3407B	SOT-23	Ø180mm	8 mm	3000 units

### Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	-30	V
Gate-Source Voltage	$V_{GS}$	±20	V
Drain Current-Continuous	$I_D$	-4.1	A
Drain Current-Pulsed (Note 1)	$I_{DM}$	-20	A
Maximum Power Dissipation	$P_D$	1.4	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	°C

### Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	90	°C/W
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### Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-30	-33	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-24V, V_{GS}=0V$	-	-	-1	μA

Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =-250μA	-1	-1.5	-3	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-4.1A	-	55	65	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-4A	-	75	95	mΩ
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =-5V,I <sub>D</sub> =-4.1A	5.5	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C <sub>Iss</sub>	V <sub>DS</sub> =-15V,V <sub>GS</sub> =0V, F=1.0MHz	-	700	-	PF
Output Capacitance	C <sub>Oss</sub>		-	120	-	PF
Reverse Transfer Capacitance	C <sub>Rss</sub>		-	75	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =-15V,R <sub>L</sub> =3.6Ω V <sub>GS</sub> =-10V,R <sub>GEN</sub> =3Ω	-	9	-	nS
Turn-on Rise Time	t <sub>r</sub>		-	5	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	28	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	13.5	-	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =-15V,I <sub>D</sub> =-4A,V <sub>GS</sub> =-10V	-	14	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	3.1	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	3.	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =-1A	-	-	-1.2	V

## Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production

## TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

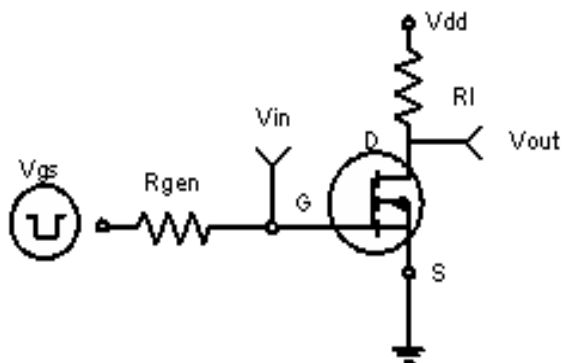


Figure 1: Switching Test Circuit



Figure 2: Switching Waveforms

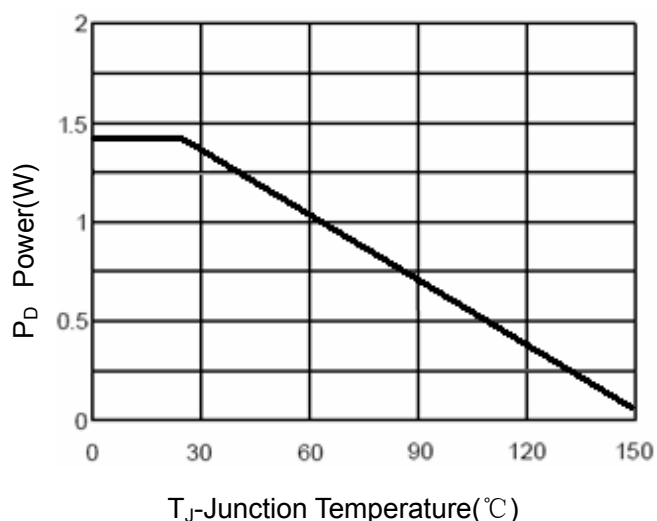


Figure 3 Power Dissipation

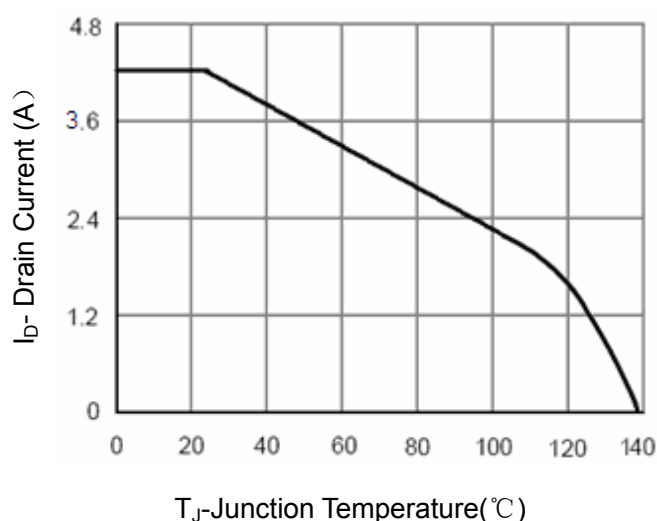


Figure 4 Drain Current

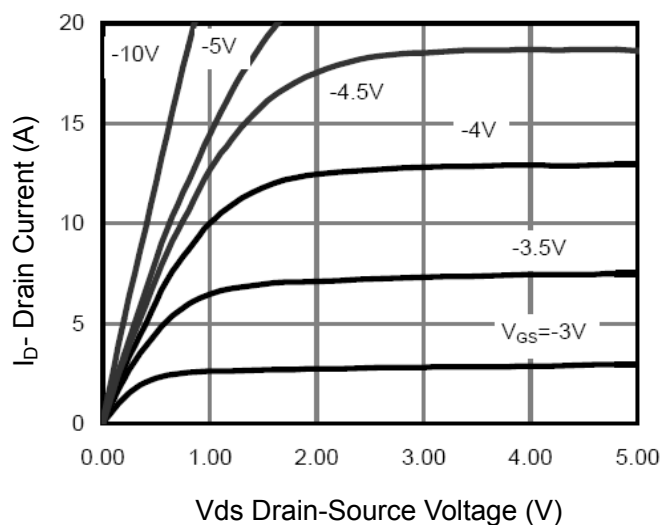


Figure 5 Output CHARACTERISTICS

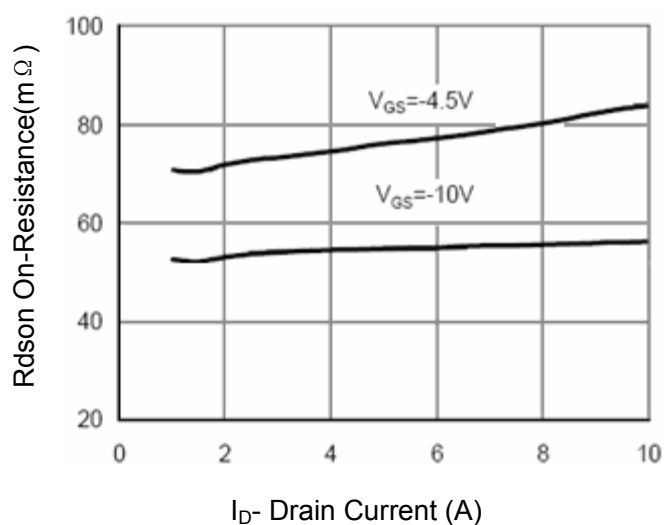
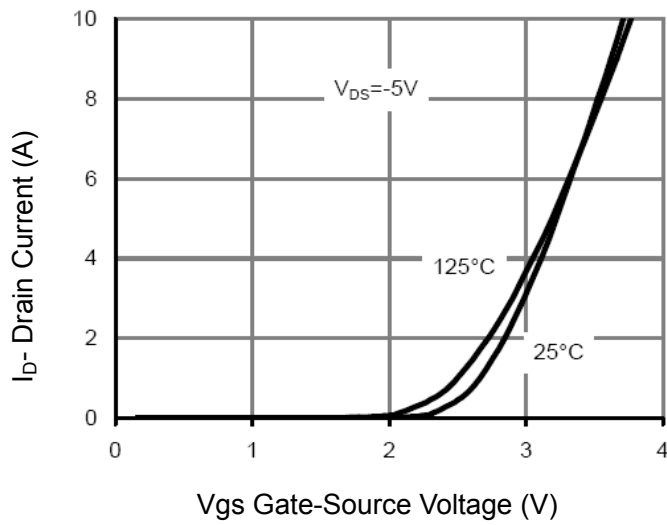
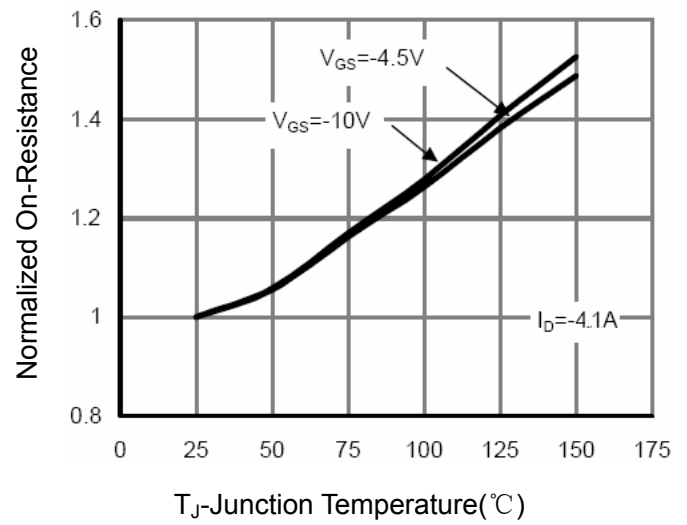


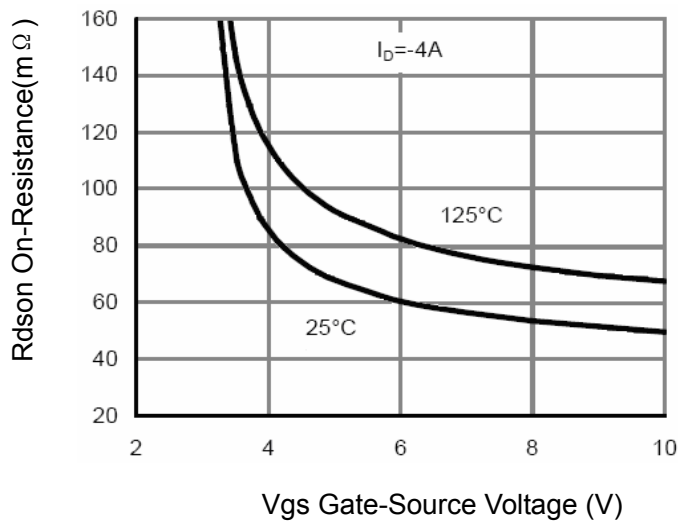
Figure 6 Drain-Source On-Resistance



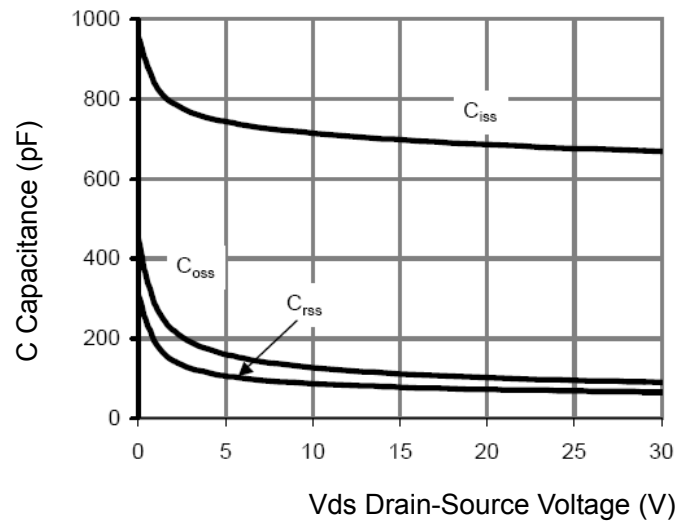
**Figure 7 Transfer Characteristics**



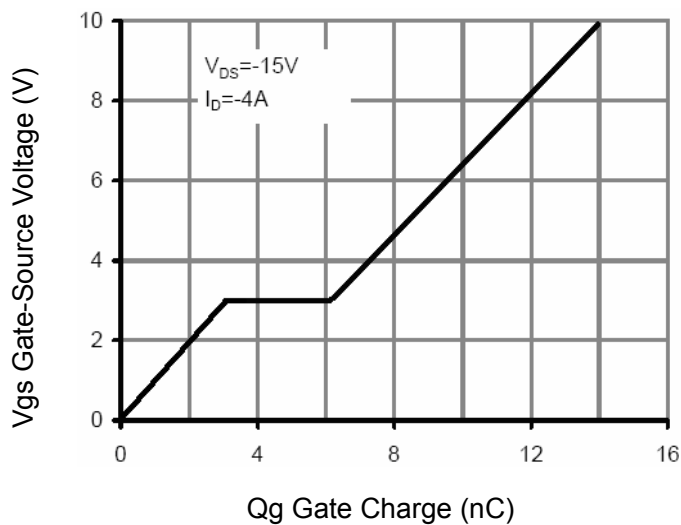
**Figure 8 Drain-Source On-Resistance**



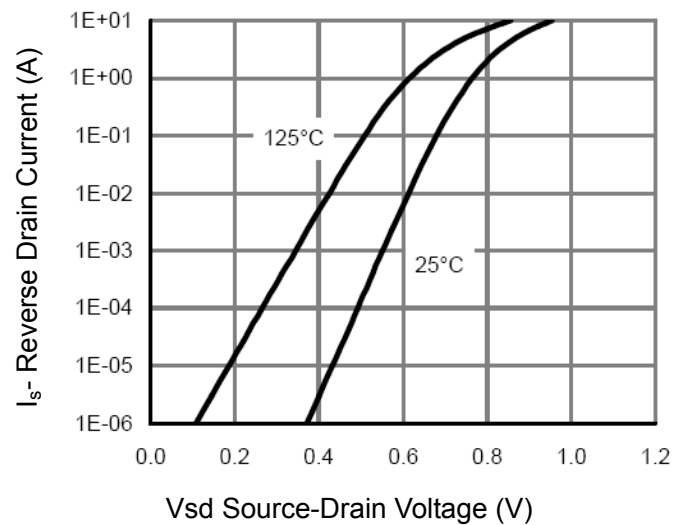
**Figure 9 Rdson vs Vgs**



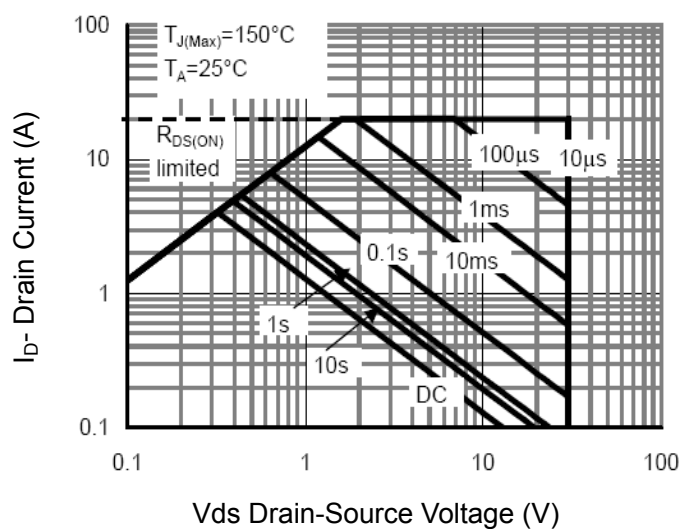
**Figure 10 Capacitance vs Vds**



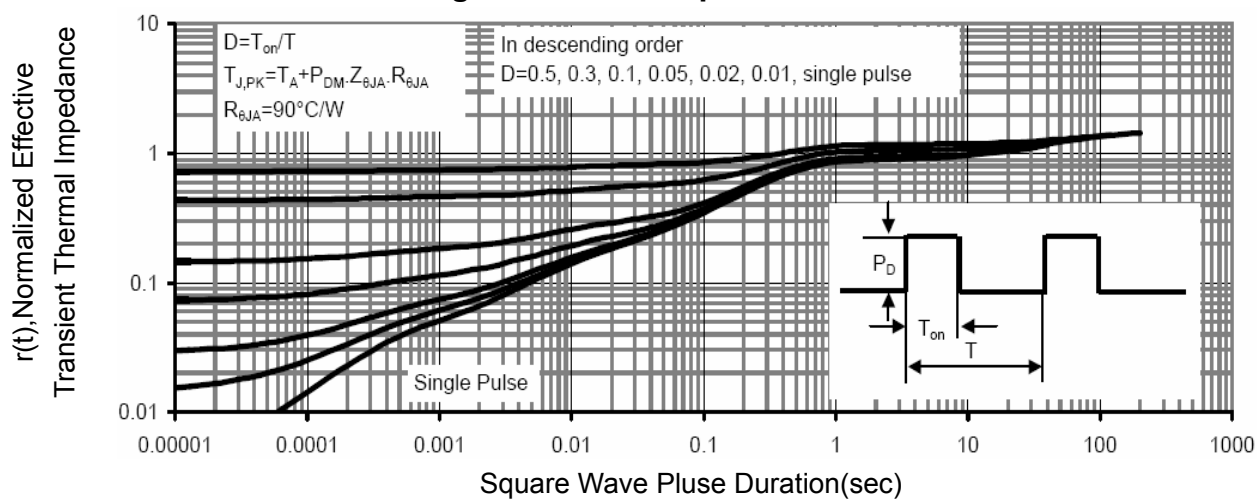
**Figure 11 Gate Charge**



**Figure 12 Source- Drain Diode Forward**



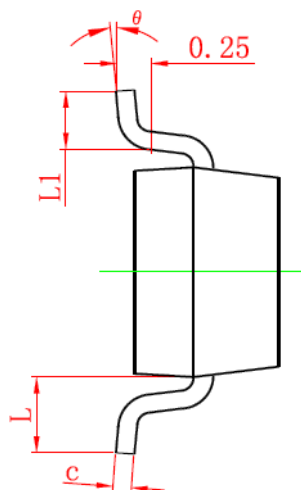
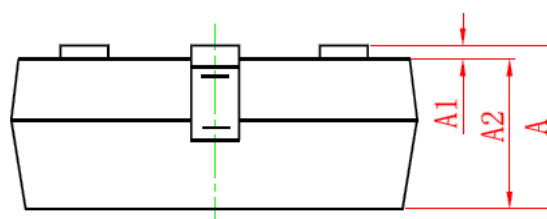
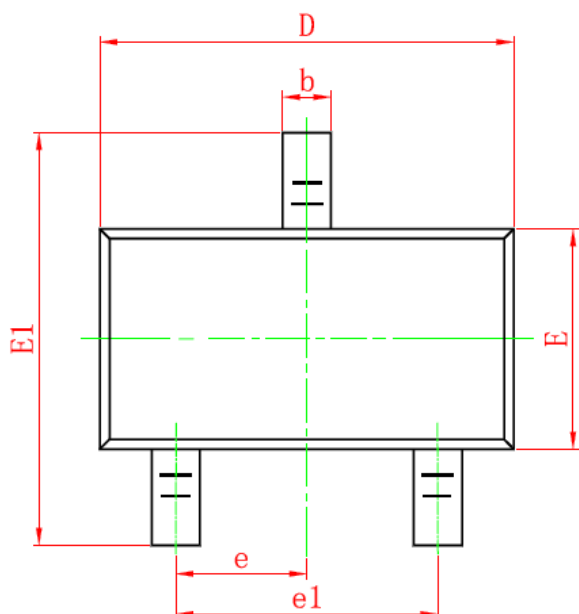
**Figure 13 Safe Operation Area**



**Figure 14 Normalized Maximum Transient Thermal Impedance**

## SOT-23 PACKAGE INFORMATION

Dimensions in Millimeters (UNIT:mm)



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°

### NOTES

1. All dimensions are in millimeters.
2. Tolerance  $\pm 0.10\text{mm}$  (4 mil) unless otherwise specified
3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
4. Dimension L is measured in gauge plane.
5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.

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